



# PRODUCT/PROCESS CHANGE NOTIFICATION

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PCN APG-PTS/14/8573

Dated 11 Jul 2014

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**L9958 Family : Activation of Catania 8" Wafer Fab and  
Copper Wire Conversion (Au 3mils to Cu 2.5mils)**

**Table 1. Change Implementation Schedule**

Forecasted implementation date for change	30-Sep-2014
Forecasted availability date of samples for customer	31-Jul-2014
Forecasted date for <b>STMicroelectronics</b> change Qualification Plan results availability	15-Sep-2014
Estimated date of changed product first shipment	10-Oct-2014

**Table 2. Change Identification**

Product Identification (Product Family/Commercial Product)	L9958, L9958XP
Type of change	Package assembly process change, Waferfab additional location
Reason for change	Company RoadMap
Description of the change	We are going to activate Catania 8 inches wafer fab (CT8) on line UP41 (products L9958, L9958XP) and change the wire bonding replacing 3 mils gold (Au) wires with 2.5 mils copper (Cu) wires. Package involved are PowerSO-20 (L9958) and PowerSSO-24 (L9958XP)
Change Product Identification	Dedicated Finished-Good Codes
Manufacturing Location(s)	1]Agrate Ag8 2]St Muar - Malaysia

## DOCUMENT APPROVAL

Name	Function
Pernigotti, Elena Maria	Marketing Manager
Cassani, Fabrizio	Product Manager
Pintus, Alberto	Q.A. Manager

## **L9958 Family: Activation of Catania 8" Wafer Fab and Copper Wire Conversion (Au 3mils to Cu 2.5mils)**

### **WHAT:**

We are going to activate Catania 8 inches wafer fab (CT8) on line UP41 (products L9958, L9958XP) and change the wire bonding replacing 3 mils gold (Au) wires with 2.5 mils copper (Cu) wires. Package involved are PowerSO-20 (L9958) and PowerSSO-24 (L9958XP) .

Together with Catania dual source activation, we are going to release a new silicon version (Metal Change) in order to improve the CPK for one specific parameter. The same metal change has already been implemented on the metal option product (running at rate 2Mpcs/Y) on both Agrate and Catania silicon, showing good CPK.

Risk Assessment: the performance of the metal option product currently in production did not show any issue. Based on this evaluation we are planning to apply the same metal change modification together with the Dual Source activation.

### **WHY:**

Company Roadmap

### **HOW:**

-ESD/LU tests and Electrical distributions will be performed in order to qualify the change.  
See enclosed document for details.

### **WHEN:**

Change will be implemented according the following schedule:

Availability of samples: End of July 2014

Qualification results: Mid of September 2014

Implementation date for change: End of September 2014



# UP41

## L9958 & L9958XP

- Copper Wire Conversion (Au 3mil to Cu 2.5mil)
- Activation of Catania Diffusion Plant

July 2014

# UP41 – L9958 & L9958XP

## ID Card

UP41

- Commercial Product: L9958 & L9958XP
- Technology: BCD6s (Agrate Diffusion Plant)
- Package: PowerSO20 & PowerSSO24 (Muar Assy Plant)
- Bonding: 3.0mil Au & 1.3mil Au

- ❑ UP41 is a metal option of UM31 product.
- ❑ UM31 is diffused in Agrate and Catania Plants, and assembled in Muar Plant in PowerSO20 and PowerSSO24 packages.

# UP41 – L9958 & L9958XP

## Description of the change

- ❑ For capacity increase and manufacturing flexibility we are going to activate Catania WaferFab as additional diffusion Plant beside Agrate
- ❑ In order to improve the CPK for one specific parameter, we take the opportunity of the dual source activation to release a new silicon version (Metal Change), already implemented on the metal option product (UM31).
- ❑ Progressing on the activities related to copper wire bonding introduction, we are going to replace all 3mil Au wires with 2.5mil Cu wires.  
Thin Au wires (1.3mil) will not be converted to Cu.
- ❑ As announced in PCN APG/13/7949 “Standardization of second bond tip design for PowerSO20 leadframe”, we are going to adopt this solution in combination with copper wire bonding introduction on UP41 PowerSO20 package

# Qualification Plan

- ❑ 2.5mil copper wire on BCD6s technology (Agrate & Catania Plant) on both PowerSO20 and PowerSSO24 packages is already qualified (Test Vehicle: UM31)  
No need to perform any reliability exercise for copper wire introduction on UP41, as full similarity is applicable.
- ❑ BCD6s technology is already qualified in Catania diffusion Plant (Test Vehicle: UM31).  
For UP41 Catania silicon validation, the only required stress tests according to AEC-Q100 guidelines, for each package, are:
  - ESD & Latch-Up
  - Electrical Characterization



# UM31 (PSO20) – Catania silicon qualification

## Reliability results summary

The reliability results are summarized in the following paragraphs.  
All the parts have been tested in according to AEC-Q100.

### UM31-CG5 BCD6S-CTM8 / PSO20 Hitachi resin – Muar (lot 5138582)

Test name	Conditions		Results Fails/Samples	Note
PC (JL3)	24h bake at 125°C, 192h at 30°C / 60% R.H., 3 reflow ( $T_{peak}=245^{\circ}\text{C}$ )		0/430	Before HTOL, PTC, THB, HTRB, TC, AC
HTOL	See schematic	$T_j=150^{\circ}\text{C}$ , $t=1000$ h	0/77	1
PTC	See schematic	$T_j= -40^{\circ}\text{C} / +150^{\circ}\text{C}$ , $t=1000$ h	0/45	1
THB	See schematic	$T_a= 85^{\circ}\text{C}$ , R.H.= 85%, $t=1000$ h	0/77	
HTRB	See schematic	$T_j=150^{\circ}\text{C}$ , $t=1000$ h	0/45	1
TC		$T_a= -50^{\circ}\text{C} / 150^{\circ}\text{C}$ , $n=1000$ cy	0/77	2, 3
AC		$T_a= 121^{\circ}\text{C}$ , $P=2.08$ atm, $t=96$ h	0/77	2
HTSL		$T_a= 150^{\circ}\text{C}$ , $t=1000$ h	0/45	4
ESD	HBM		>3	5
ESD	CDM		>3	6
LU	CI / SO	JEDEC 78 Class 1, $I=\pm 100$ mA $T=125^{\circ}\text{C}$	>3	

#### Notes

- <sup>1</sup> No significant drift observed after drift analysis
- <sup>2</sup> Visual inspection showed good results
- <sup>3</sup> SAM analysis and WBP after TC 1000 cy: passed
- <sup>4</sup> WBP after HTSL 1000 h: passed

#### <sup>5</sup> HBM details

$\pm 4\text{kV}$	cumulative stress only pins 6,8,13	passed
$\pm 2\text{kV}$	cumulative stress	passed
$\pm 1\text{kV}$	cumulative stress	passed
$\pm 2\text{kV}$	Allpins vs GND	passed
$\pm 2\text{kV}$	Allpins vs VPS	passed
$\pm 2\text{kV}$	Allpins vs VDD	passed
$\pm 2\text{kV}$	Allpins vs VDDIO	passed
$\pm 2\text{kV}$	IO vs IO	passed
$\pm 2\text{kV}$	IO,NC vs IO,NC	passed
$\pm 2\text{kV}$	NC vs PW	passed

#### <sup>6</sup> CDM details

$\pm 750\text{V}$	corner pins (1, 10, 11, 20)	passed
$\pm 500\text{V}$	Allpins	3 FAIL
$\pm 400\text{V}$	Allpins	3 FAIL

# UM31 (PSSO24) – Catania silicon qualification

## Reliability results summary

The reliability results are summarized in the following paragraphs.  
All the parts have been tested in according to AEC-Q100.

### UM31-CG5 BCD6S-CTM8 / PwSSO24 Hitachi resin – Muar (lot 5129744)

Test name	Conditions		Results Fails/Samples	Note
<b>PC (JL3)</b>	24h bake at 125°C, 192h at 30°C / 60% R.H., 3 reflow (T <sub>peak</sub> =260°C)		0/430	Before HTOL, PTC, THB, HTRB, TC, AC
<b>HTOL</b>	See schematic	T <sub>j</sub> =150°C, t=1000 h	0/77	1
<b>PTC</b>	See schematic	T <sub>j</sub> = -40°C / +150°C, t=1000 h	0/45	1
<b>THB</b>	See schematic	T <sub>a</sub> = 85°C, R.H.= 85%, t=1000 h	0/77	
<b>HTRB</b>	See schematic	T <sub>j</sub> =150°C, t=1000 h	0/45	1
<b>TC</b>		T <sub>a</sub> = -50°C / 150°C, n=1000 cy	0/77	2, 3
<b>AC</b>		T <sub>a</sub> = 121°C, P=2.08 atm, t=96h	0/77	
<b>HTSL</b>		T <sub>a</sub> = 150°C, t=1000 h	0/45	
<b>ESD</b>	<b>CDM</b>		>3	4

#### Notes

- <sup>1</sup> No significant drift observed after drift analysis
- <sup>2</sup> Visual inspection showed good results
- <sup>3</sup> SAM analysis and WBP after TC 1000 cy: passed

#### <sup>4</sup> CDM details

±750V	corner pins	passed
±500V	Allpins	FAIL
±400V	Allpins	passed
±300V	Allpins	passed

# UM31 (PSO20) – 2.5mil Cu Wire Bonding

## Reliability results summary

### Reliability test conditions and results

TEST NAME	CONDITIONS [SPEC]	REJ / S.S.				NOTES
		AG8 NN	CT 8 LL	CT 8 HH	CT 8 NN	
JL3	24h bake @ 125°C 192h @ 30°C / 60% RH reflow simulation (3 times) at T <sub>MAX</sub> =245°C [IPC/Jedec J-STD-020D]	0/164	0/164	0/164	0/85	1
JL3 + TC	T <sub>A</sub> =-50/+150°C, 1000 cycles T <sub>A</sub> =-50/+150°C, 1000 cycles	0/87 0/77	0/87 0/77	0/87 0/77	-	1, 2, 3
HTSL	T <sub>A</sub> =150°C, 1000 h T <sub>A</sub> =150°C, 2000 h	0/55 0/45	0/55 0/45	0/55 0/45	-	2
JL3 + ES	100 TC (-65/+150°C) + 96h AC (2atm, 121°C)	0/77	0/77	0/77	-	2, 3
JL3 + THB	T <sub>A</sub> =85°C, RH=85% 2000h	-	-	-	0/77	
WBP	As per reference specification	0/5	0/5	0/5	-	
WBS	As per reference specification	0/5	0/5	0/5	-	

#### NOTES:

- <sup>1</sup> SAM analysis after JL3 preconditioning and TC shows no delamination at the molding compound interfaces with chip passivation and inner lead fingers. Physiological and uncritical delamination has been observed at die-pad interface (no down-bonding).
- <sup>2</sup> Wire bonding strength after the stress has been successfully verified through wire-pull test: neither abnormal break loads, nor forbidden failure modes have been detected.
- <sup>3</sup> Visual and/or SEM inspection after the stress test have pointed out no remarkable degradation of silicon passivation, metal interconnects and wire bonds.

# UM31 (PSSO24) – 2.5mil Cu Wire Bonding

## Reliability results summary

### *Reliability test conditions and results*

TEST NAME	CONDITIONS [SPEC]	REJ / S.S.		NOTES
		AG8 NN	CT 8 NN	
JL3	24h bake @ 125°C 192h @ 30°C / 60% RH reflow simulation (3 times) at T <sub>MAX</sub> =245°C [IPC/Jedec J-STD-020D]	0/259	0/259	1
JL3 + TC	T <sub>A</sub> =-50/+150°C, 1000 cycles T <sub>A</sub> =-50/+150°C, 2000 cycles	0/87 0/77	0/87 0/77	1, 2, 3, 4
HTSL	T <sub>A</sub> =150°C, 1000 h T <sub>A</sub> =150°C, 2000 h	0/55 0/45	0/55 0/45	2
JL3 + ES	100 TC (-65/+150°C) + 96h AC (2atm, 121°C)	0/77	0/77	2, 3
JL3 + THB	T <sub>A</sub> =85°C, RH=85% 1000h	-	0/80	
WBP	As per reference specification	0/5	0/5	
WBS	As per reference specification	0/5	0/5	

#### NOTES:

- <sup>1</sup> SAM analysis after JL3 preconditioning and TC shows no delamination at the molding compound interfaces with chip passivation, and a minor delamination on lead-frame Ag-plated inner tips later assessed through the below-reported destructive items. Physiological and uncritical delamination has been also observed at the die-pad interface (no down-bonding allowed).
- <sup>2</sup> Wire bonding strength after the stress has been successfully verified through wire-pull test: neither abnormal break loads, nor forbidden failure modes have been detected.
- <sup>3</sup> Visual and/or SEM inspection after the stress test have pointed out no remarkable degradation of silicon passivation, metal interconnects and wire bonds.
- <sup>4</sup> Bond-pads of stressed units have been de-layered (so-called “cratering test”) until the base insulating oxide (BPSG) in order to exclude latent cracks propagation to the underlying silicon.



## Public Products List

PCN Title : L9958 Family : Activation of Catania 8" Wafer Fab and Copper Wire Conversion (Au 3mils to Cu 2.5mils)

PCN Reference : APG-PTS/14/8573

PCN Created on : 05-AUG-2014

Subject : Public Products List

Dear Customer,

Please find below the Standard Public Products List impacted by the change:

### ST COMMERCIAL PRODUCT

L9958  
L9958XPTR

L9958TR

L9958XP

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